

ABSTRACT OF THE DISCLOSURE

A magnetoresistive effect element (1) has an arrangement in which a pair of ferromagnetic material layers (magnetization fixed layer (5) and magnetization free layer (7)) is opposed to each other through an intermediate layer (6) to obtain a magnetoresistive change by causing a current to flow in the direction perpendicular to the layer surface, the magnetization free layer (7) is made of a ferromagnetic material containing FeCoB or FeCoNiB and the magnetization free layer (7) has a film thickness ranging from 2 nm to 8 nm. A magnetic memory device comprises this magnetoresistive effect element (1) and bit lines and word lines sandwiching the magnetoresistive effect element (1) in the thickness direction. There are provided the magnetoresistive effect element having satisfactory magnetic characteristics and the magnetic memory device including this magnetoresistive effect element and which can obtain excellent write/read characteristics.